

ABSTRACT OF THE DISCLOSURE

A structure of a CMOS image sensory device is described. A photodiode sensory region and a transistor device region are isolated from each other by an isolation layer formed in the substrate. A gate structure is located on the transistor device region, and a
5 source/drain region is in the transistor device region beside the side of the gate structure. A doped region is in the photodiode sensory region. A self-aligned block is located on the photodiode sensory region and a protective layer is formed on the entire substrate.

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